

Supplemental Amendment  
U.S. APPLN. NO. 09/881,782

**REMARKS**

The above corrects minor informalities in new claims 21 and 22 added in the Amendment

Under 37 C.F.R. § 1.111 filed June 14, 2002.

Respectfully submitted,



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**APPENDIX**

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS:**

**The claims are amended as follows:**

21. (Amended) A group-III nitride semiconductor light-emitting diode comprising at least a first conduction-type single crystal substrate provided with a first conduction-type back-surface ohmic electrode on a back surface thereof, a buffer layer comprising a boron phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure on said buffer layer, and a window layer comprising an electrically conducting transparent oxide crystal layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer and is disposed in an open light-emitting region other than a projective region of [the] a pad electrode on the surface of said group-III nitride crystal layer [and a], the pad electrode for wire bonding is on the center of the upper surface of said window layer, and wherein a sum of areas of said second conduction-type surface ohmic electrodes is from 5 to 30% of a total area of said open light-emitting region.

22. (Amended) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure,

and a window layer comprising an electrically conducting transparent oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and is disposed in an open light-emitting region other than a projective region of a pad electrode on the surface of said group-III nitride crystal layer and comes into contact with the surface of said group-III nitride crystal layer, and said pad electrode for wire bonding is on the center of the upper surface of said window layer, wherein a sum of areas of said surface ohmic electrodes is from 5 to 30% of a total area of the open light-emitting region.